

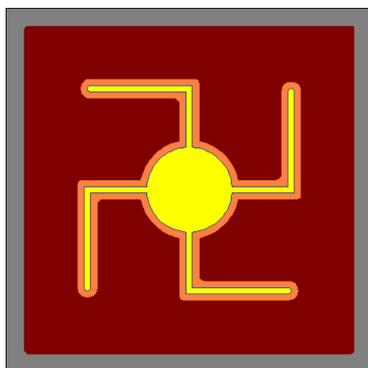


014MR-U-FF1

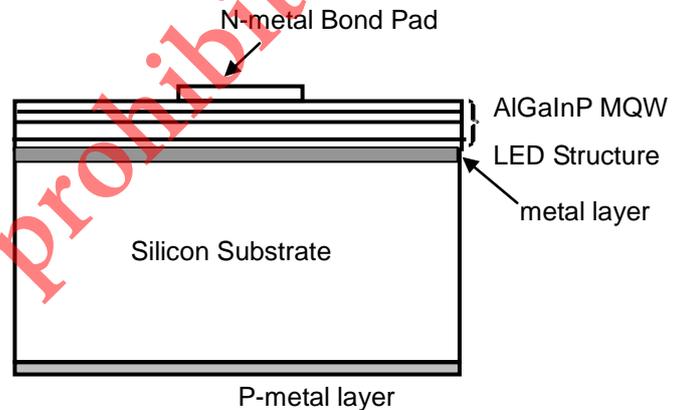
1. Descriptions:

014MR-U is a reddish-orange LED chip made from Aluminum Gallium Indium Phosphide (AlGaInP) MOCVD process and bonded with Silicon. It is fabricated by the HPO's proprietary metal Bonding mechanism, 014MR-U is featured by homogeneous and high light output at all sides with superior beam pattern. Excellent performance under sunlight and reliable life-long stability make 014MR-U ideal for both lighting and outdoor applications.

2. Chip Diagram:



Chip pattern



Chip Side view

3. Chip characteristics:

| | |
|-------------------|---------------------|
| Substrate | Si |
| Emitting material | AlGaInP |
| p-pad electrode | Au-alloy |
| n-pad electrode | Au-alloy |
| Chip size | 360±25um x 360±25um |
| Chip thickness | 150±25um |
| Pad Diameter | 84±15um |



4. Electrical and Optical Characteristics(Ta=25°C):

| Parameter | Condition *1 | Symbol | Min. | Typ. | Max. | Unit |
|-----------------------|----------------------|-----------------|------|------|------|------|
| Forward voltage | I _F =20mA | V _{F1} | 1.8 | 2.1 | 2.4 | V |
| Threshold voltage | I _F =10uA | V _{F3} | 1.3 | 1.5 | 1.8 | V |
| Reverse current | V _R =5V | I _R | - | - | 10.0 | uA |
| Peak wavelength | I _F =20mA | λ _p | 620 | - | 650 | nm |
| Dominant wavelength | I _F =20mA | λ _d | 615 | - | 640 | nm |
| Half width *2 | I _F =20mA | Δλ | - | 15 | - | nm |
| Luminous Intensity *3 | I _F =20mA | LOP | 500 | - | - | mcd |

Note:

- *1 I_F : DC Forward current V_R : Reverse voltage
- *2 Value of Half width is only for reference
- *3 Luminous Intensity is measured by HPO's equipment on bare chips.
- 4 Characteristic curves are measured on standard TO-46 package type without encapsure.

5. Characteristic Curves:

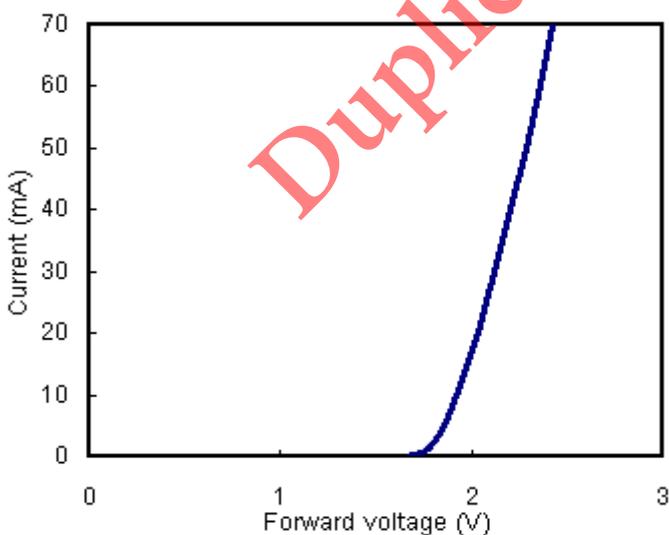


Fig.1 The I-V characteristics (0-70mA)

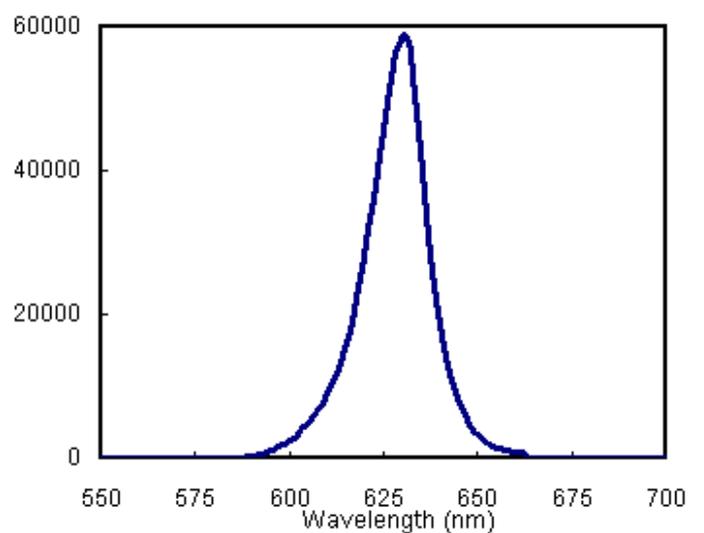


Fig.2 The EL spectrum

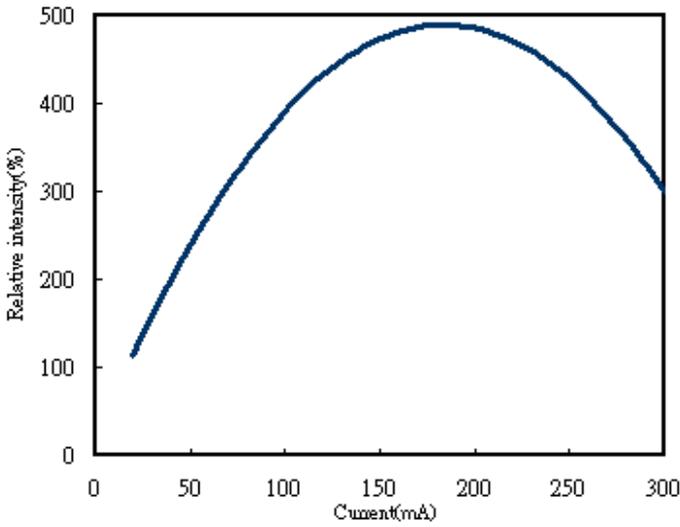


Fig.3 Relative intensity vs forward current

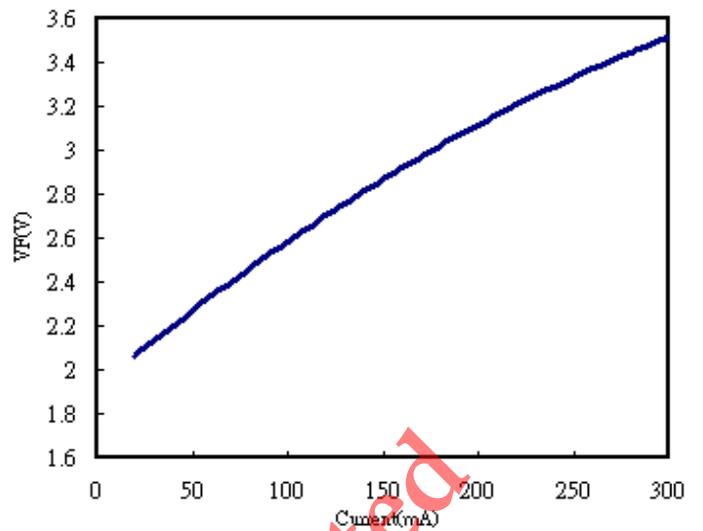


Fig.4 The V-I characteristics (0-300mA)

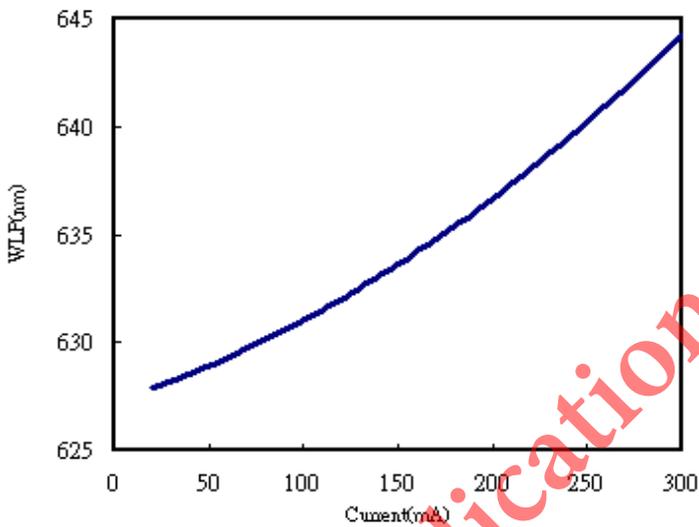


Fig.5 The WLP shift vs forward current

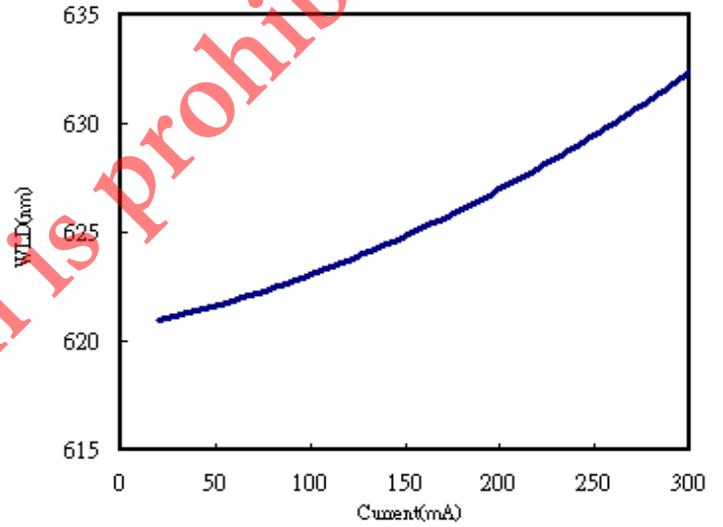


Fig.6 The WLD shift vs forward current

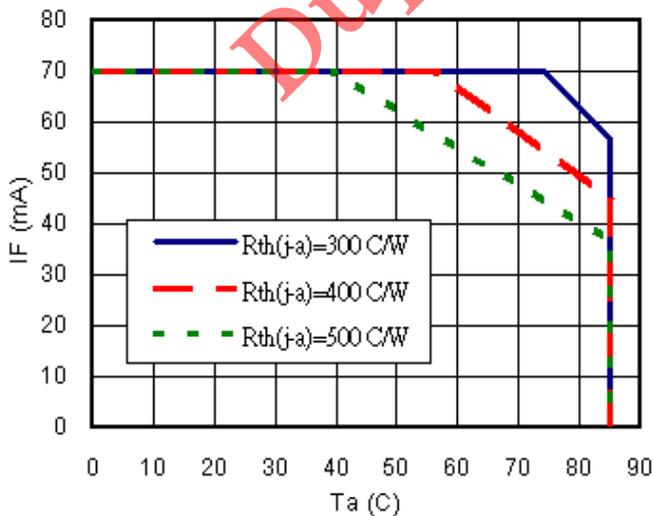


Fig.7 Derating curve based on $T_j(\text{max})=125^\circ\text{C}$

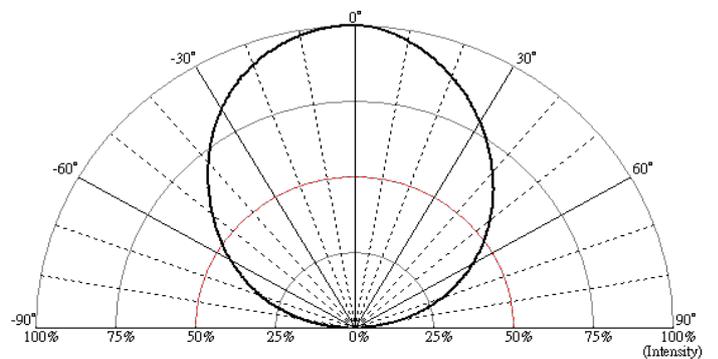


Fig.8 Light pattern and view angle of bare chip

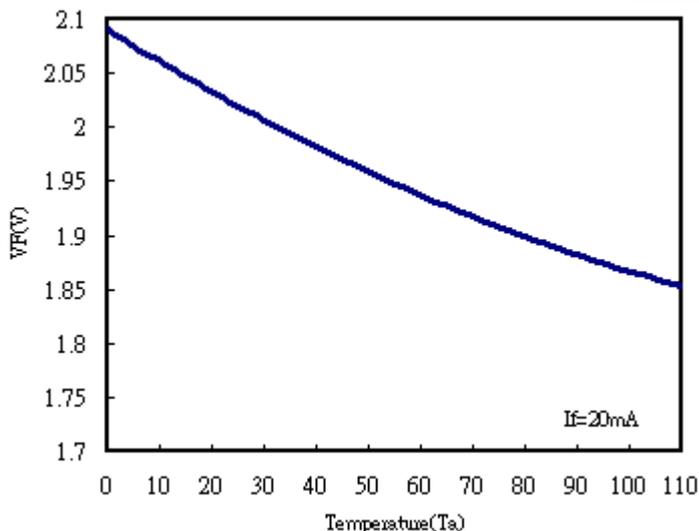


Fig.9 The forward voltage vs Ta(°C)

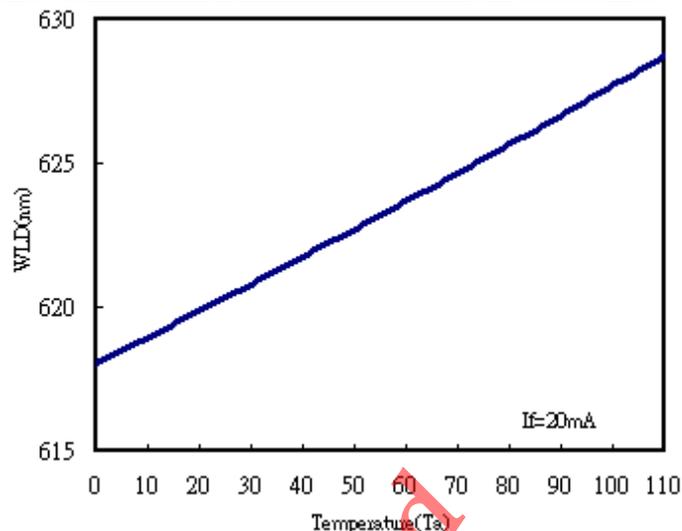


Fig.10 The WLD shift vs Ta(°C)

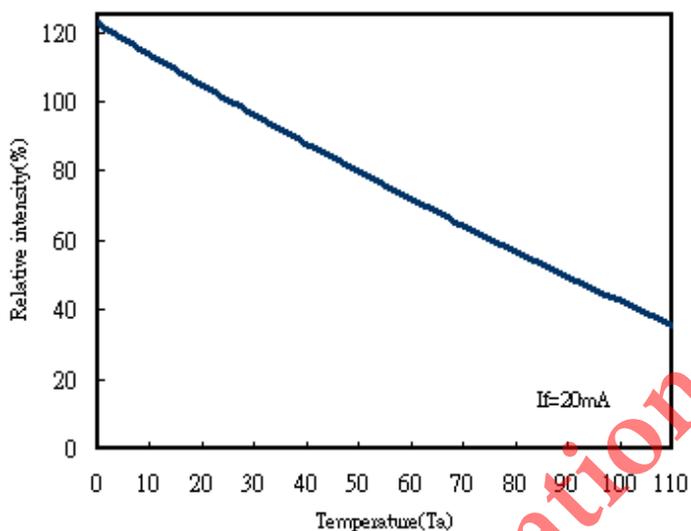


Fig.11 Relative intensity vs Ta(°C)

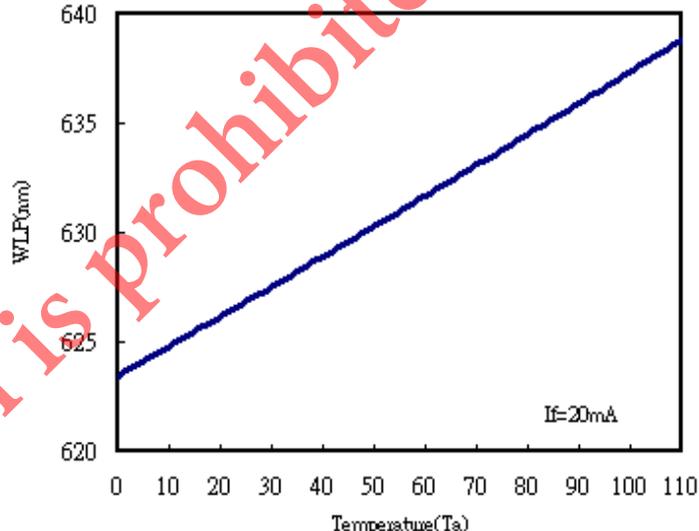


Fig.12 The WLP shift vs Ta(°C)

6. Absolute Maximum Ratings(Ta=25°C):

| Parameter | Symbol | Condition | Rating |
|------------------------------|-------------------|-----------------------------|----------------|
| DC Forward Current | I _F | Ta=25°C | ≤ 70mA |
| Peak Pulsing Current | I _{peak} | 1/10 duty cycle @ 1kHz | ≤ 150mA |
| Reverse Voltage | V _R | Ta=25°C | ≤ 10V |
| Operating Temperature Range | T _{OP} | - | -40°C to +85°C |
| Storage Temperature Range | T _{stg} | Chip-on-tape/storage | +5°C to +30°C |
| | | Chip-on-tape/transportation | -20°C to +65°C |
| LED Junction Temperature | T _J | - | ≤ 125°C |
| Temperature during Packaging | - | - | 280°C (<10sec) |

Note: Maximum ratings are package dependent. The above maximum ratings were determined using a Metal Core Printed Circuit Board(MCPCB) without an encapsulant. Stress in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.